
EECS 427

Lecture 3: CMOS review II

Reading: 3.1, 3.2, 5.1-5.4, 6.2

Recap

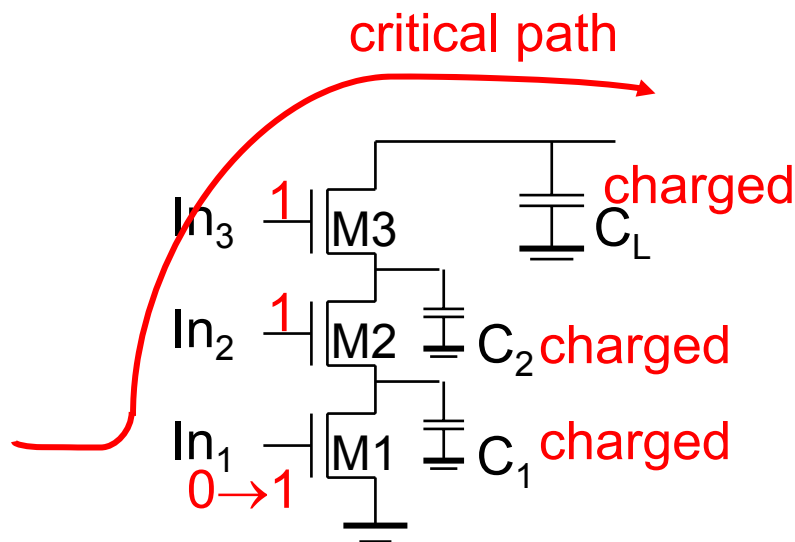
- CMOS review I
 - Basic transistor operation
 - Inverter DC transfer curve
 - CMOS logic driving load capacitance
 - Delay calculation
 - Simplified RC charging/discharging model
 - Dependence of gate size on delay
 - Gate sizing motivation

Outline

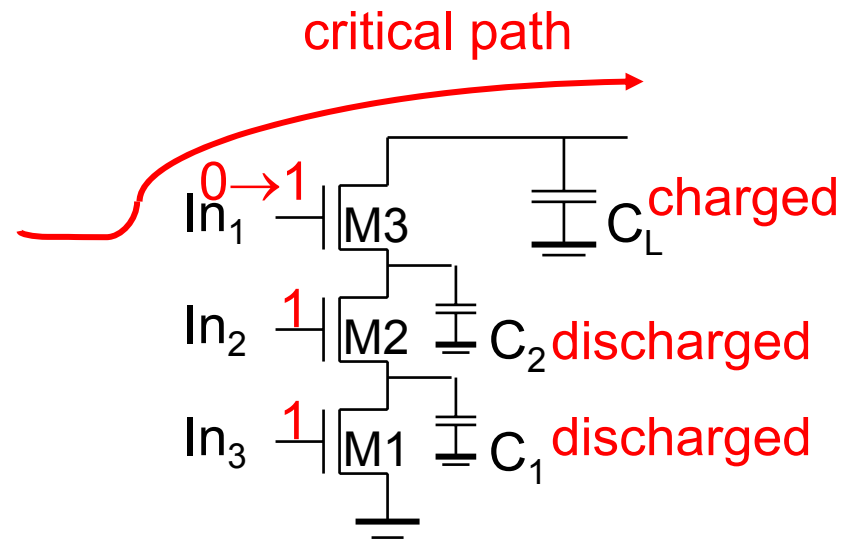
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Fast Complex Gates: Design Techniques

- Transistor ordering to set critical path input closest to output



delay determined by time to discharge C_L , C_1 and C_2

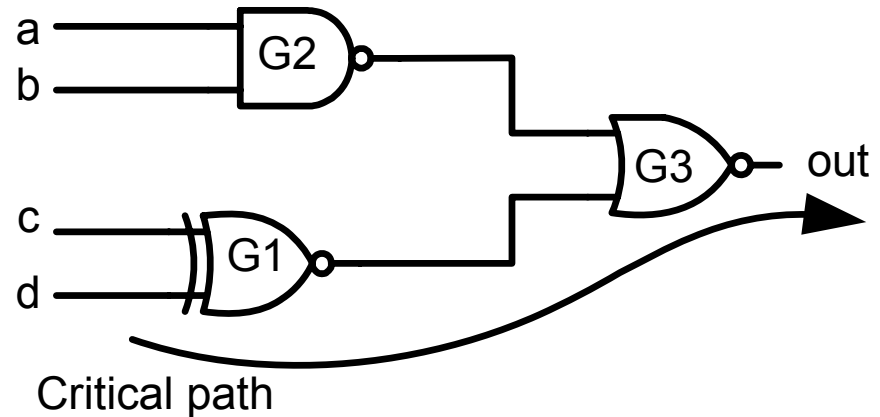


delay determined by time to discharge C_L

Fast Complex Gates:

Design Techniques- Asymmetric Gates

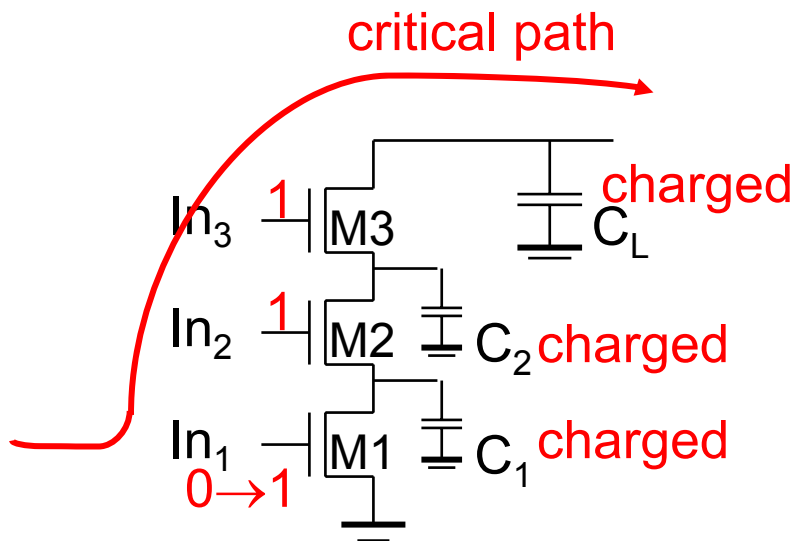
- Critical path is from c/d to output
- Why should gate delay for G3 be equal for both pins?
- Size up one input
 - Increases load capacitance of that pin
 - Improves drive strength of gate



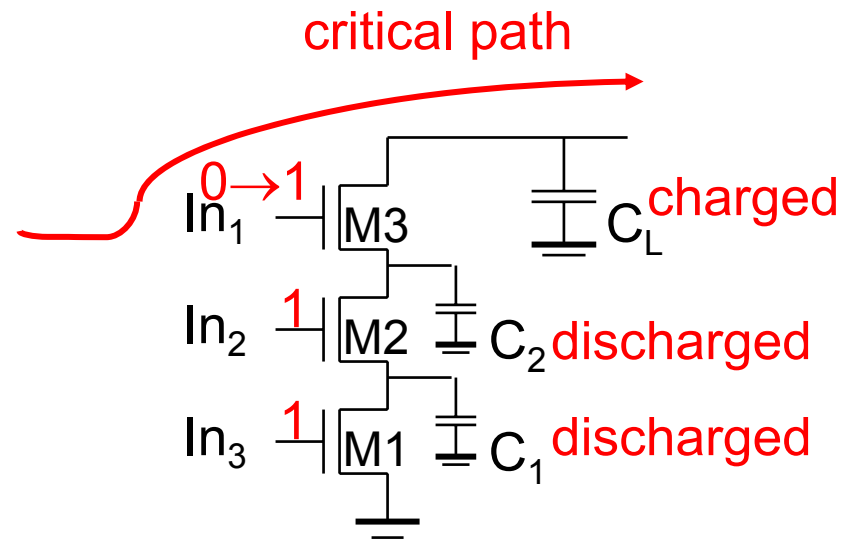
A – out = 100ps
B – out = 120ps
C – out = 200ps
D – out = 200ps

Fast Complex Gates: Pin - ordering

- Pin corresponding to critical path nearest to output



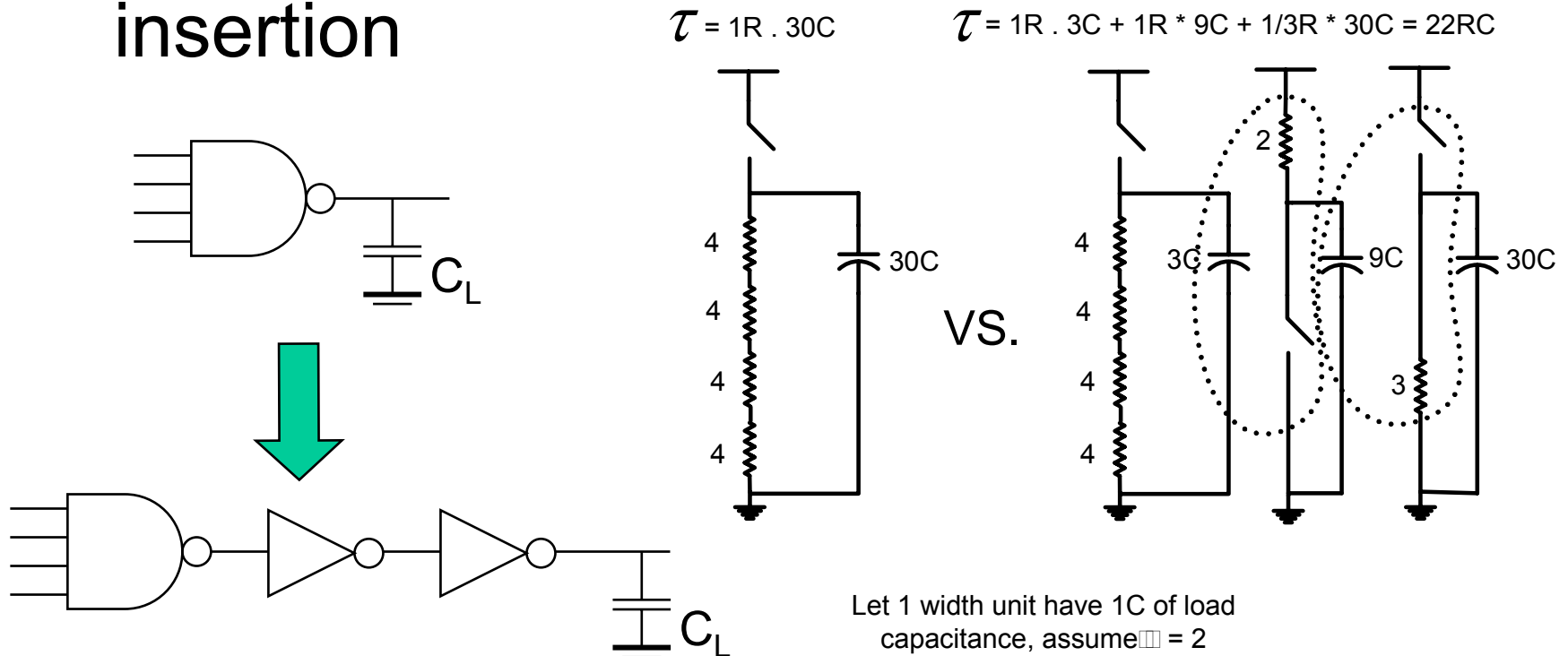
delay determined by time to discharge C_L , C_1 and C_2



delay determined by time to discharge C_L

Fast Complex Gates: Design Techniques

- Isolating fan-in from fan-out using buffer insertion

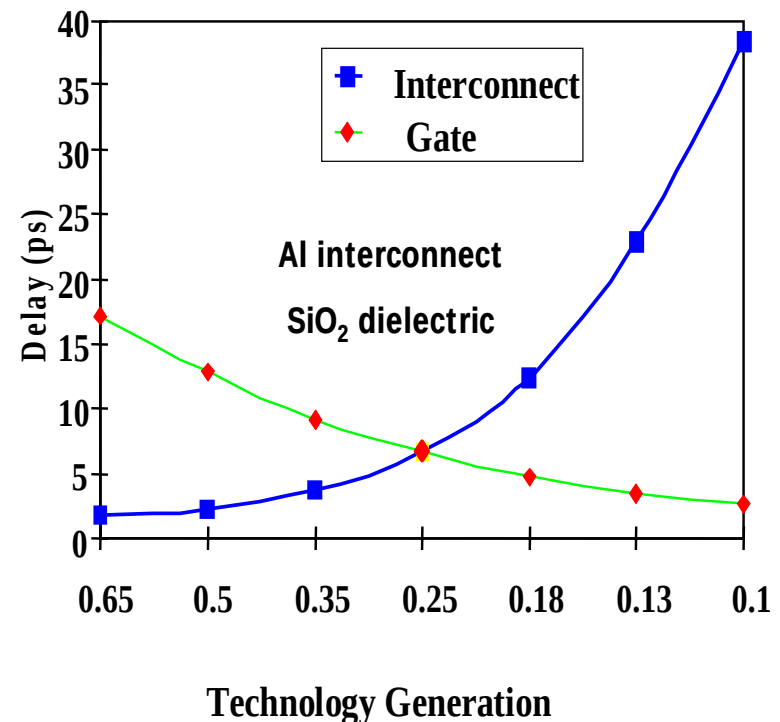


Recommended evaluations

- Calculate the β ratio in your process
- Compute I_{dsat} and V_{dsat} for NMOS and PMOS devices
- Calculate the approximate gate capacitance per micron for NMOS and PMOS devices
- Calculate unit inverter delay ($W_n=1\mu$, $W_p=$ for: $\beta \mu$)
 - Self-loading
 - 10 micron of M1 wire with adjacent metal
 - Driving 4 copies of itself

Interconnect

- Gate delays reduce with technology scaling
- Global interconnect delays increase with scaling
 - Interconnects must be included in analysis and optimization



Interconnect Parasitics

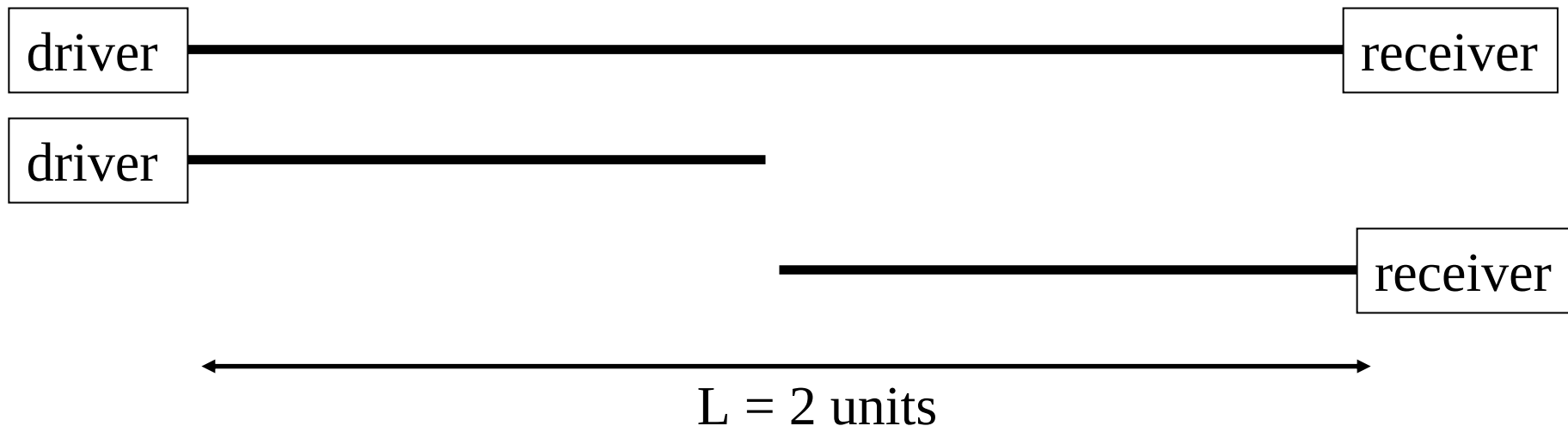
- Classes of parasitics
 - Capacitance
 - Resistance
 - Inductance (627 focuses on this)
- Impact of interconnect parasitics
 - Increases propagation delay
 - Energy dissipation
 - Loss in power distribution
 - Reliability and signal integrity
 - Clock-skew

Interconnect Modeling

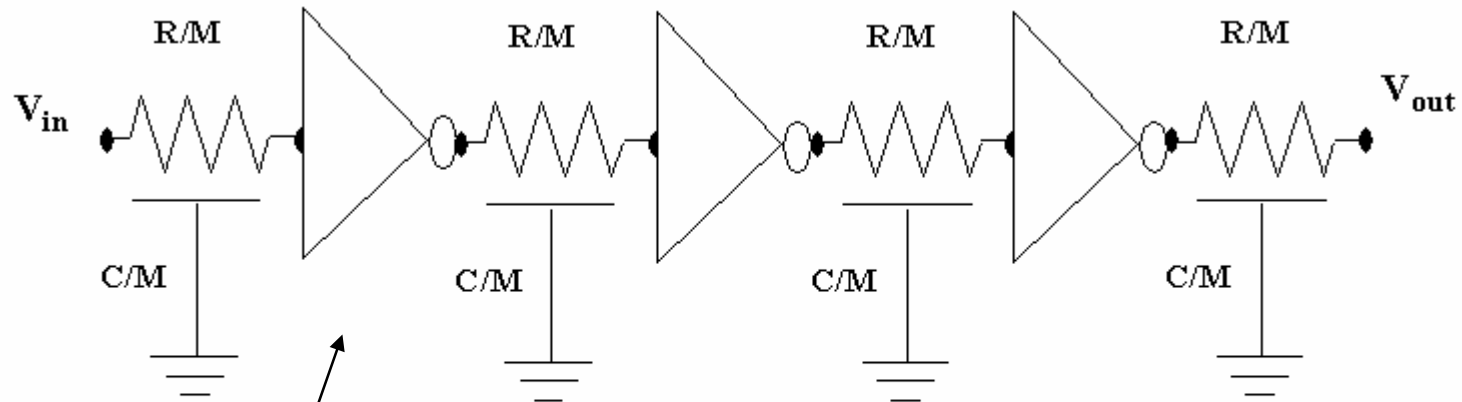
- Lumped capacitance model is what we use for device/gate analysis
- Lumped RC model
 - For simple one segment RC:
 - 50% Delay = $0.69 \cdot RC$
 - 10-90% Slew = $2.2 \cdot RC$
- Distributed RC line model
 - More accurate for interconnect analysis
 - 50% Delay = $0.38 \cdot RC$
 - 10-90% Slew = $0.9 \cdot RC$
- Either way, wire delay is quadratic with wire length

How to reduce RC delay

- Since RC delay is quadratic with length, reducing length is key
- Note: $2^2 = 4$ and $1+1 = 2$ but $1^2 + 1^2 = 2$



Repeaters

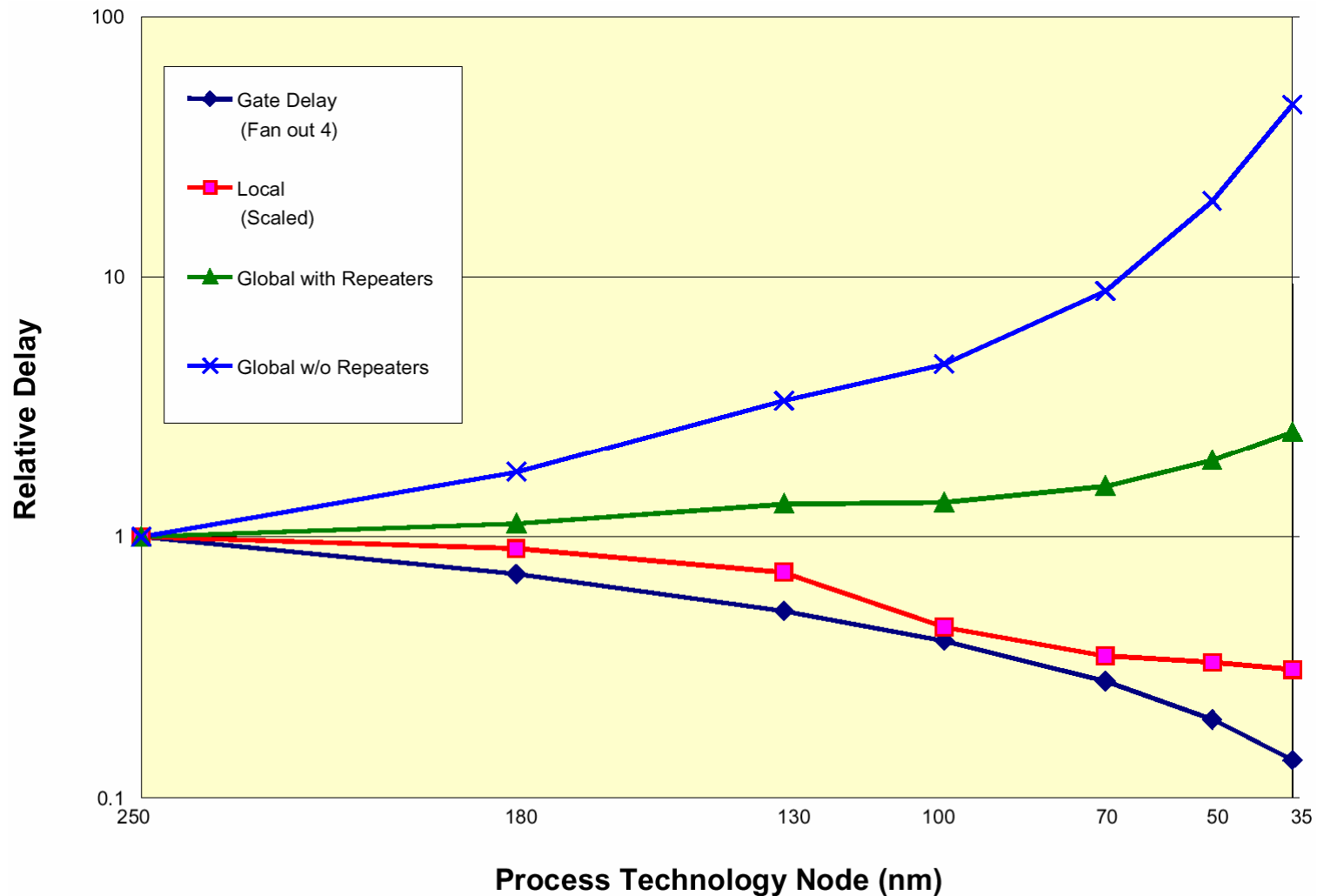


Repeater

Repeater = strong driver (usually an inverter or pair of inverters for non-inverting polarity) placed along a long RC line to “break up” the line and reduce delay

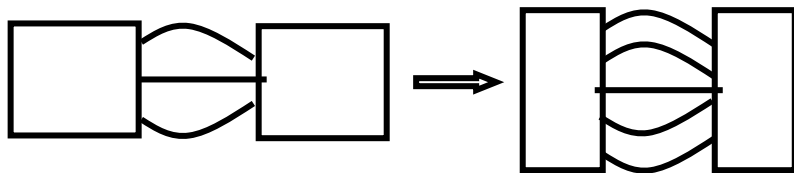
We need to determine optimal # of repeaters and their size based on wire and device delay properties

Repeaters Impact

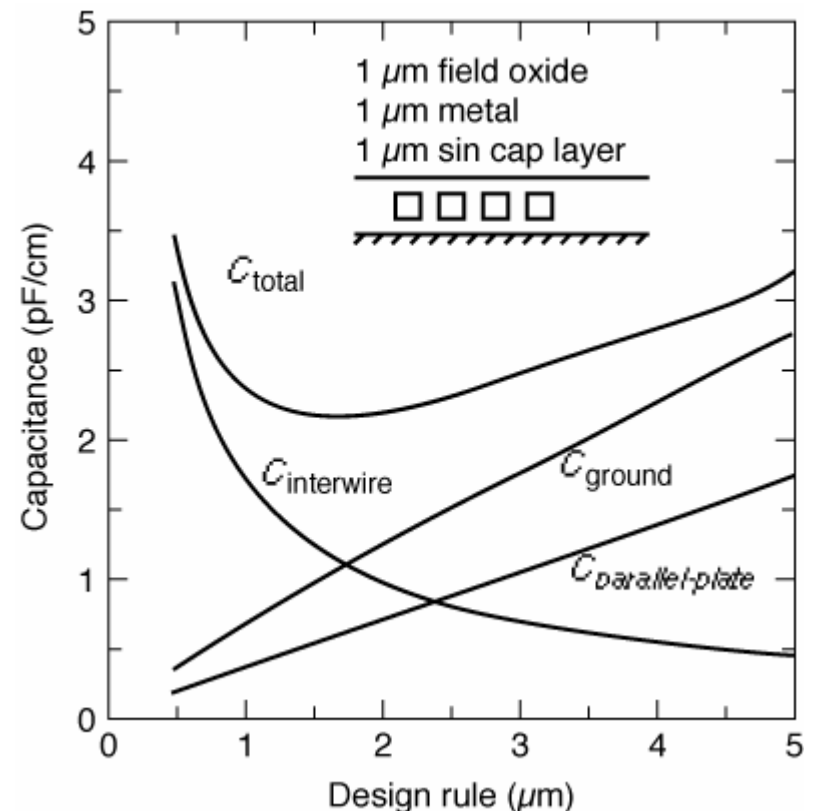


Coupling Capacitance

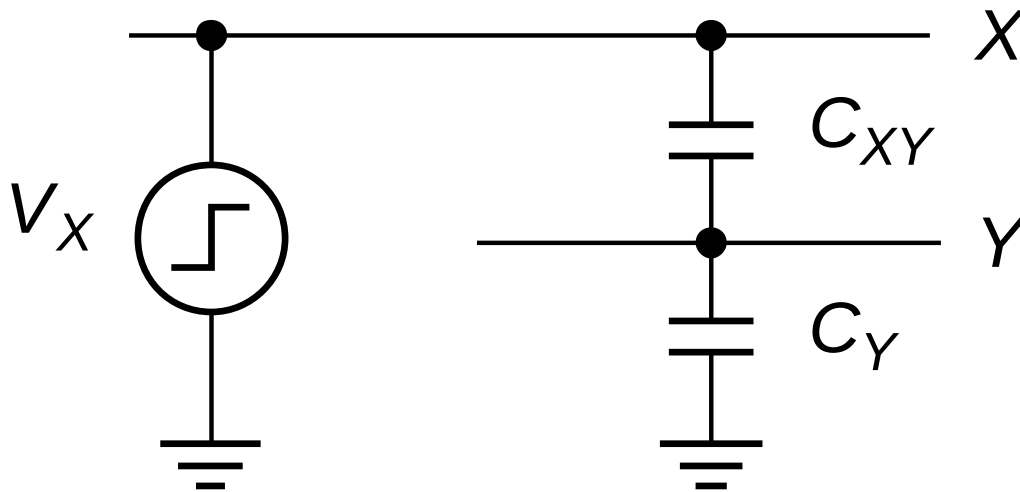
- To reduce interconnect resistance, thickness is not scaled as aggressively as the width of the interconnect



- Tall wires (high aspect ratios)

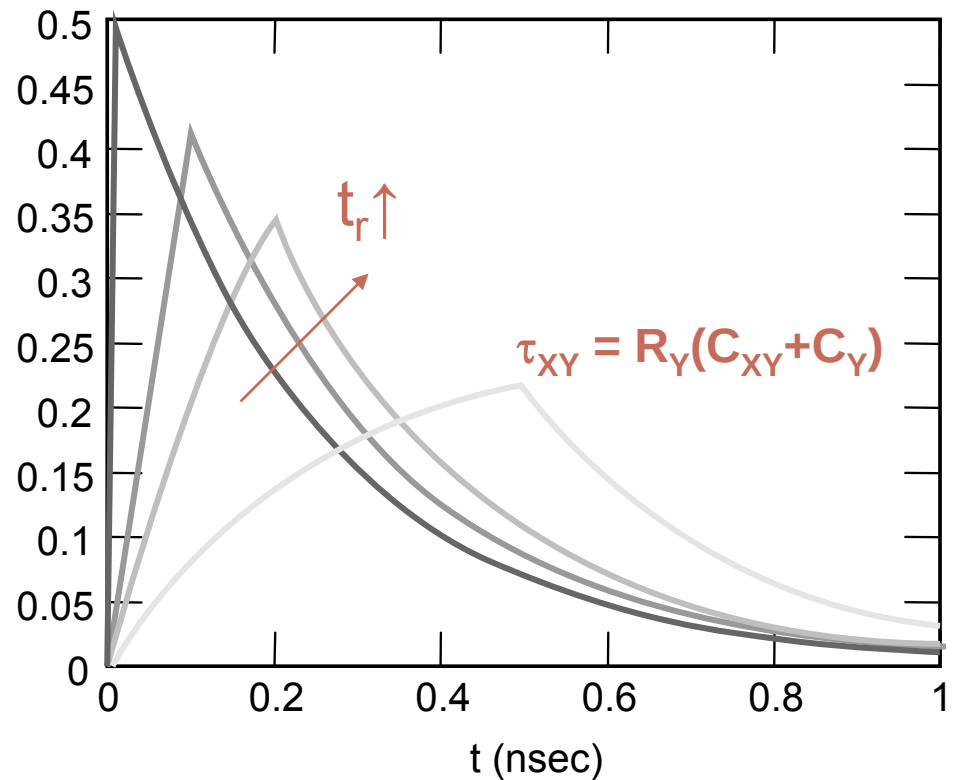
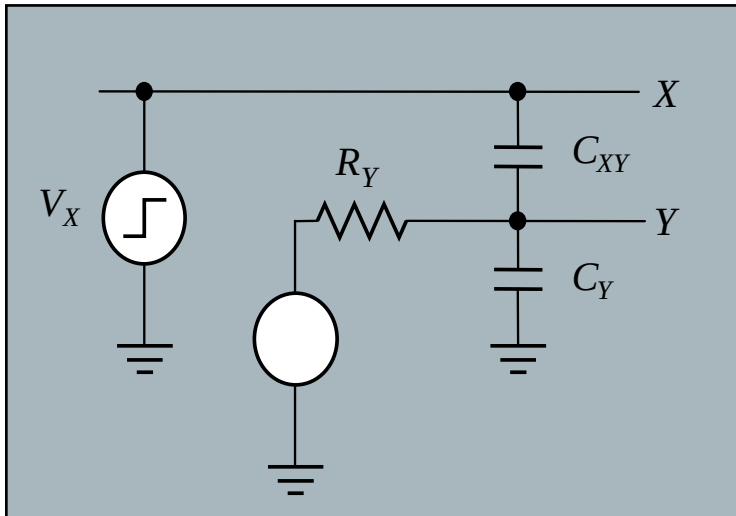


Capacitive Cross Talk



$$\Delta V_Y = \frac{C_{XY}}{C_Y + C_{XY}} \Delta V_X$$

Capacitive Cross Talk

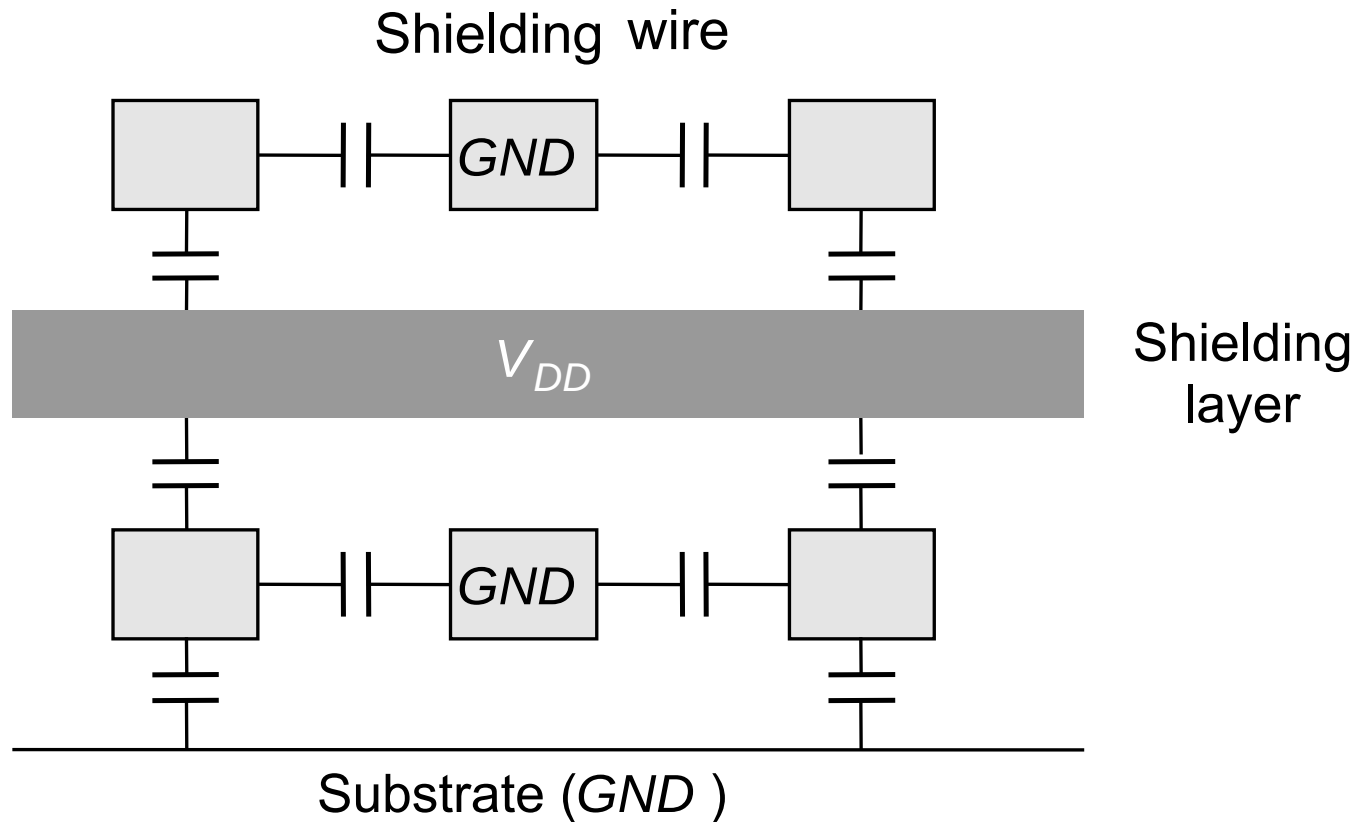


Keep time-constant small (size up driver of node Y)

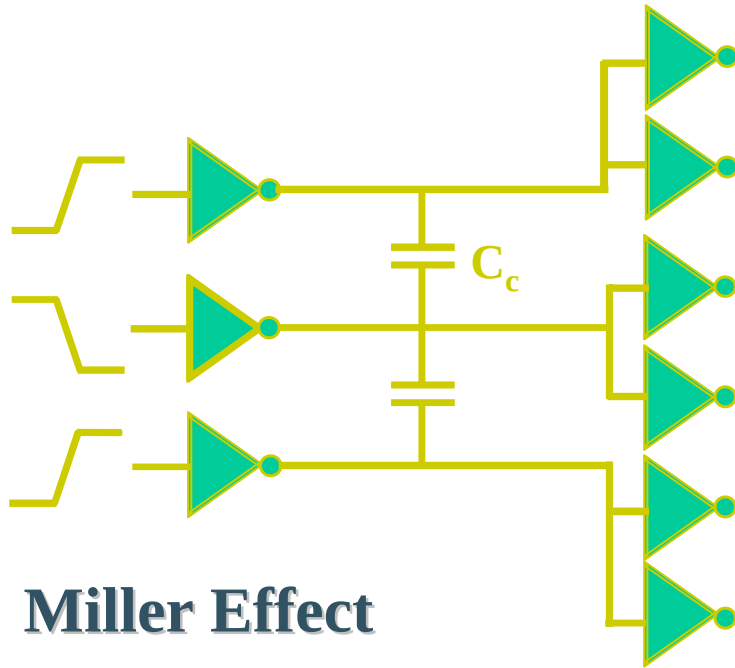
Dealing with Capacitive Cross Talk

- Avoid floating nodes (keepers!)
- Protect sensitive nodes (keep wires short)
- Make rise and fall times as large as possible
- Do not run wires together for a long distance
- Use shielding wires
- Use shielding layers

Shielding



Impact of Crosstalk on Delay



DELAY DEPENDENT UPON
ACTIVITY IN NEIGHBORING
WIRES! (very important today)

Miller Effect

- Both terminals of capacitor are switched in opposite directions ($0 \rightarrow V_{dd}$, $V_{dd} \rightarrow 0$)
- Effective voltage is doubled and additional charge is needed (from $Q=CV$)